

HiPerFET™

Power MOSFETs

N-Channel Enhancement Mode
Avalanche Rated, High dv/dt, Low t_{rr}

IXFK 110 N06
IXFK 105 N07
IXFK 110 N07

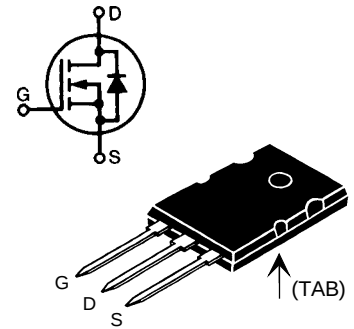
V_{DSS}	I_{D25}	$R_{DS(on)}$
60 V	110 A	6 mΩ
70 V	105 A	7 mΩ
70 V	110 A	6 mΩ

$t_{rr} \leq 250 \text{ ns}$

Symbol	Test Conditions	Maximum Ratings		
V_{DSS}	$T_J = 25^\circ\text{C}$ to 150°C	N07	70	V
		N06	60	V
V_{DGR}	$T_J = 25^\circ\text{C}$ to 150°C ; $R_{GS} = 1 \text{ M}\Omega$	N07	70	V
		N06	60	V
V_{GS}	Continuous		± 20	V
V_{GSM}	Transient		± 30	V
I_{D25}	$T_C = 25^\circ\text{C}$, die capability		110	A
I_{D130}	$T_C = 130^\circ\text{C}$, limited by external leads		76	A
I_{DM}	$T_C = 25^\circ\text{C}$, pulse width limited by T_{JM}		600	A
I_{AR}	$T_C = 25^\circ\text{C}$		100	A
E_{AR}	$T_C = 25^\circ\text{C}$		30	mJ
E_{AS}	$T_C = 25^\circ\text{C}$		2	J
dv/dt	$I_S \leq I_{DM}$, $di/dt \leq 100 \text{ A}/\mu\text{s}$, $V_{DD} \leq V_{DSS}$, $T_J \leq 150^\circ\text{C}$, $R_G = 2 \Omega$		5	V/ns
P_D	$T_C = 25^\circ\text{C}$		500	W
T_J		-55 ... +150		$^\circ\text{C}$
T_{JM}		150		$^\circ\text{C}$
T_{stg}		-55 ... +150		$^\circ\text{C}$
T_L	1.6 mm (0.063 in) from case for 10 s		300	$^\circ\text{C}$
M_d	Mounting torque Terminal connection torque	0.9/6 -	Nm/lb.in. Nm/lb.in.	
Weight			10	g

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
V_{DSS}	$V_{GS} = 0 \text{ V}$, $I_D = 1 \text{ mA}$	N06 N07	60 70	V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 8 \text{ mA}$		2	4 V
I_{GSS}	$V_{GS} = \pm 20 \text{ V}_{DC}$, $V_{DS} = 0$			$\pm 200 \text{ nA}$
I_{DSS}	$V_{DS} = 0.8 \cdot V_{DSS}$ $V_{GS} = 0 \text{ V}$	$T_J = 25^\circ\text{C}$ $T_J = 125^\circ\text{C}$		400 μA 2 mA
$R_{DS(on)}$	$V_{GS} = 10 \text{ V}$, $I_D = 0.5 \cdot I_{D25}$ Note 2	110N06/110N07 105N07		6 mΩ 7 mΩ

TO-264 AA (IXFK)



Features

- International standard packages
- JEDEC TO-264 AA, epoxy meet UL94 V-0, flammability classification
- Low $R_{DS(on)}$ HDMOS™ process
- Rugged polysilicon gate cell structure
- Unclamped Inductive Switching (UIS) rated
- Low package inductance
- Fast intrinsic Rectifier

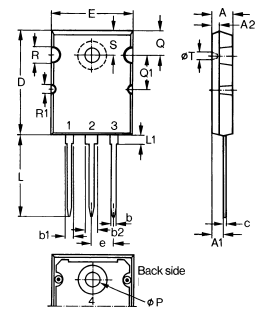
Applications

- DC-DC converters
- Synchronous rectification
- Battery chargers
- Switched-mode and resonant-mode power supplies
- DC choppers
- Temperature and lighting controls
- Low voltage relays

Advantages

- Easy to mount
- Space savings
- High power density

Symbol	Test Conditions	Characteristic Values ($T_j = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
g_{fs}	$V_{DS} = 10\text{ V}; I_D = 0.5 \cdot I_{D25}$, Note 2	60	80	S
C_{iss}	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1\text{ MHz}$		9000	pF
C_{oss}			4000	pF
C_{rss}			2400	pF
$t_{d(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{D25}$ $R_G = 1\ \Omega$ (External),		30	ns
t_r			60	ns
$t_{d(off)}$			100	ns
t_f			60	ns
$Q_{g(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{D25}$		480	nC
Q_{gs}			60	nC
Q_{gd}			240	nC
R_{thJC}	TO-264 AA		0.25	K/W
R_{thCK}	TO-264 AA	0.15		K/W

TO-264 AA Outline


Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.82	5.13	.190	.202
A1	2.54	2.89	.100	.114
A2	2.00	2.10	.079	.083
b	1.12	1.42	.044	.056
b1	2.39	2.69	.094	.106
b2	2.90	3.09	.114	.122
c	0.53	0.83	.021	.033
D	25.91	26.16	1.020	1.030
E	19.81	19.96	.780	.786
e	5.46 BSC		.215 BSC	
J	0.00	0.25	.000	.010
K	0.00	0.25	.000	.010
L	20.32	20.83	.800	.820
L1	2.29	2.59	.090	.102
P	3.17	3.66	.125	.144
Q	6.07	6.27	.239	.247
Q1	8.38	8.69	.330	.342
R	3.81	4.32	.150	.170
R1	1.78	2.29	.070	.090
S	6.04	6.30	.238	.248
T	1.57	1.83	.062	.072

Source-Drain Diode		Characteristic Values ($T_j = 25^\circ\text{C}$, unless otherwise specified)		
Symbol	Test Conditions	min.	typ.	max.
I_S	$V_{GS} = 0\text{ V}$	110N06/110N07 105N07		110 A 105 A
I_{SM}	Repetitive; pulse width limited by T_{JM}	110N06/110N07 105N07		440 A 420 A
V_{SD}	$I_F = 100\text{ A}, V_{GS} = 0\text{ V}$, Note 2			1.7 V
t_{rr}	$I_F = 25\text{ A}$ $-di/dt = 100\text{ A}/\mu\text{s}$, $V_R = 50\text{ V}$		150	250 ns
Q_{RM}				0.7 μC
I_{RM}				9 A

Note: 1. Pulse width limited by T_{JM}
2. Pulse test, $t \leq 300\ \mu\text{s}$, duty cycle $d \leq 2\%$

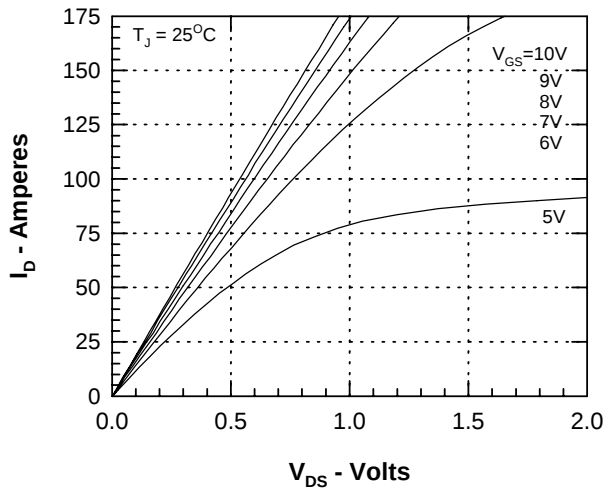


Figure 1. Output Characteristics at 25°C

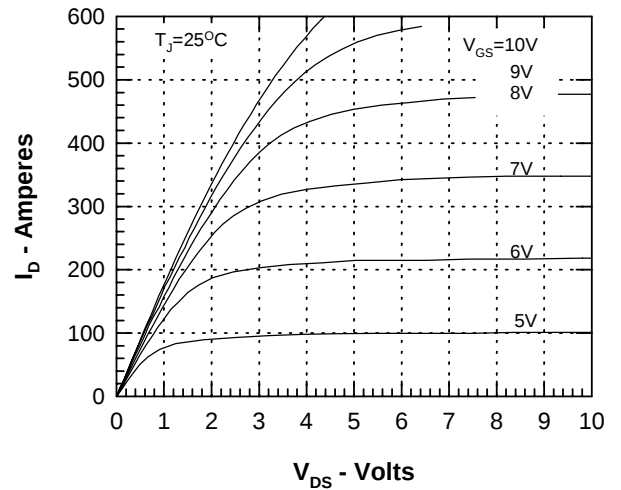


Figure 2. Extended Output Characteristics

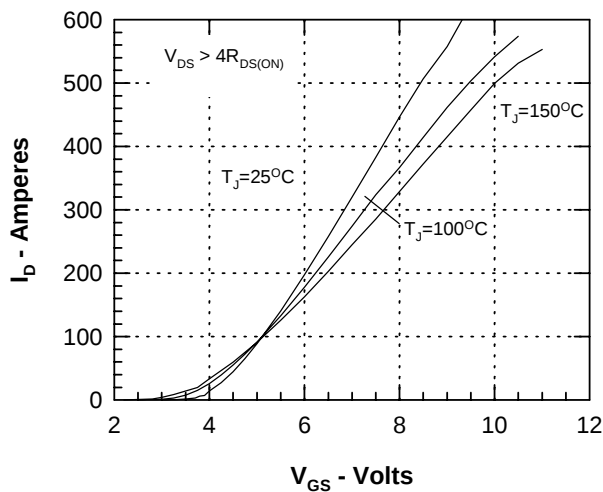


Figure 3. Admittance Curves

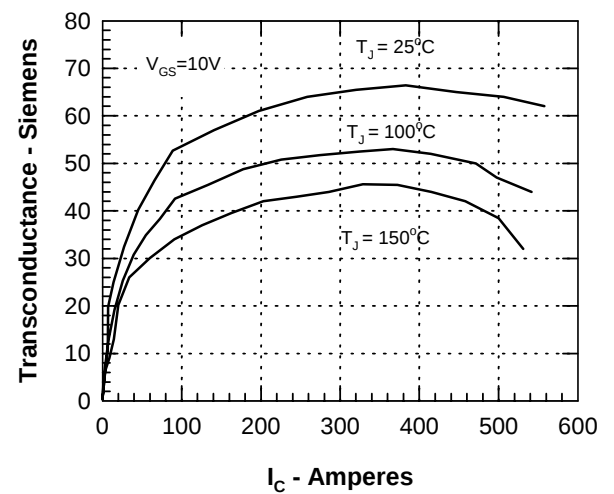
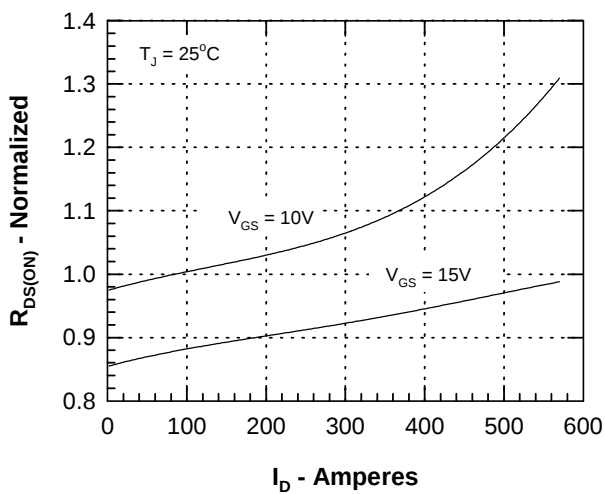
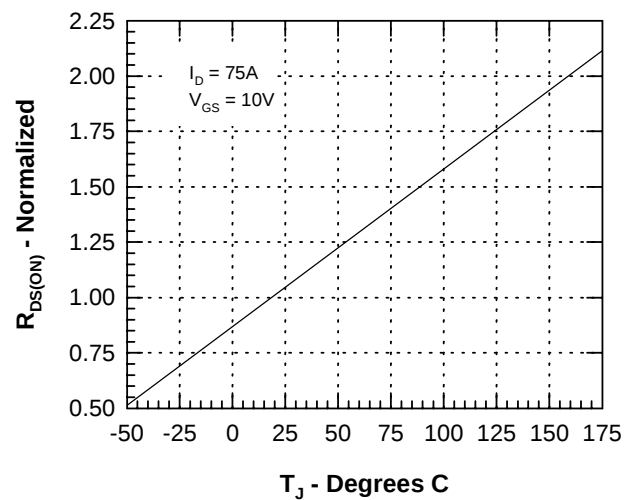


Figure 4. Transconductance vs. Drain Current


Figure 5. $R_{DS(on)}$ normalized to $0.5 I_{D25}$ value

Figure 6. Normalized $R_{DS(on)}$ vs. Junction Temperature

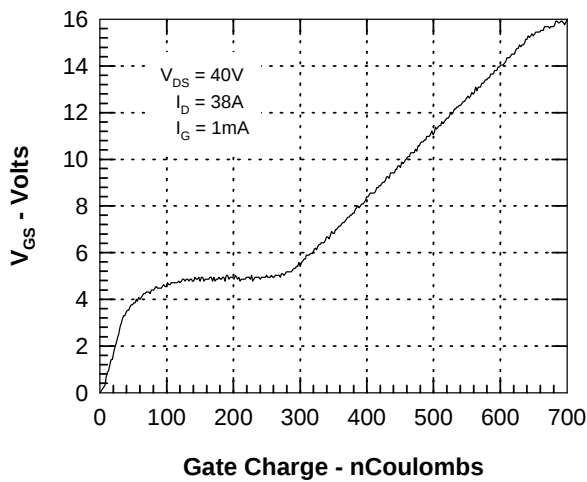


Figure 7. Gate Charge

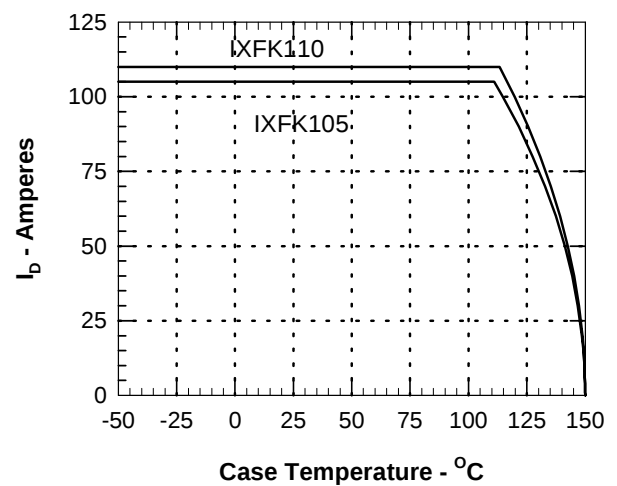


Figure 8. Drain Current vs. Case Temperature

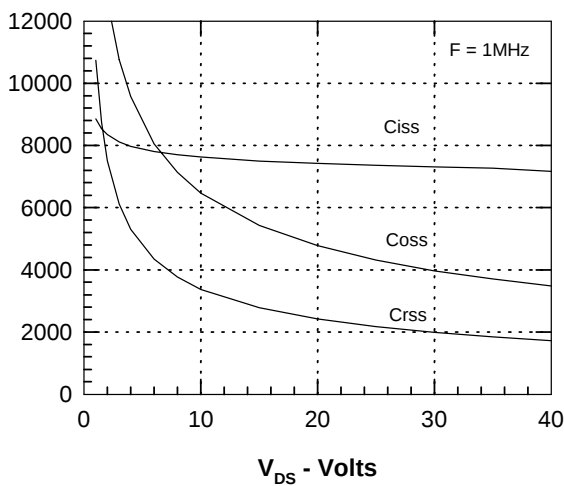


Figure 9. Capacitance Curves

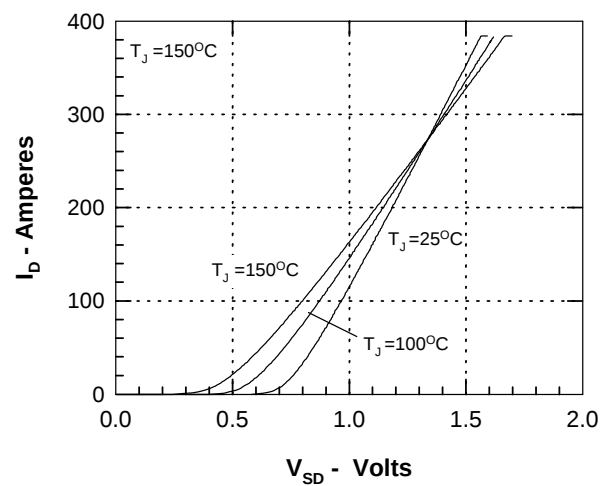


Figure 10. Source-Drain Voltage vs. Source Current

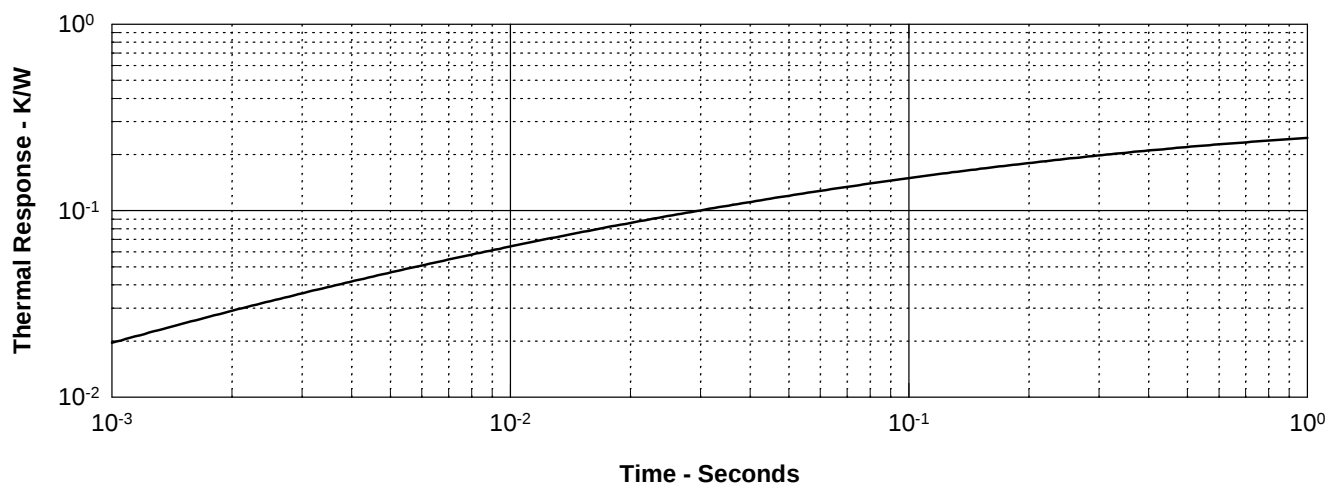


Figure 11. Transient Thermal Resistance



Disclaimer Notice - Information furnished is believed to be accurate and reliable. However, users should independently evaluate the suitability of and test each product selected for their own applications. Littelfuse products are not designed for, and may not be used in, all applications. Read complete Disclaimer Notice at www.littelfuse.com/disclaimer-electronics.